



Bipolar PNP Bare Die – BTP6998

Part Description

The BTP6998 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications. NPN complement is BTN6998.

Key Parameters:

- VCBO = -60V
- VCEO = -50V
- VEBO = -5V
- hFE = 120-400 @ VCE = -6V, IC = -0.002A
- VCE(Sat) = -0.3V @ IC = -0.1A, IB = -10mA
- fT = 80 MHz @ VCE = -10V, IE = 0A
- COBO = 2pF @ VCB = -10V

Features

Low VCE(sat). Designed to provide performance equivalent to TOSHIBA HN1B26FS

Die Size (Unawn)

260µm X 310µm, 10 Mils X 12 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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